# **ON Semiconductor**

# Is Now



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**Preferred Devices** 

# **Silicon Epicap Diodes**

Designed for general frequency control and tuning applications; providing solid-state reliability in replacement of mechanical tuning methods.

#### **Features**

- High Q with Guaranteed Minimum Values at VHF Frequencies
- Controlled and Uniform Tuning Ratio
- Available in Surface Mount Package
- Pb-Free Packages are Available

#### **MAXIMUM RATINGS** (T<sub>C</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	30	Vdc
Forward Current	I <sub>F</sub>	200	mAdc
Forward Power Dissipation  MMBV109LT1  @ T <sub>A</sub> = 25°C Derate above 25°C  MV209  @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	200 2.0 200 1.6	mW mW/°C mW mW/°C
Junction Temperature	$T_J$	+125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

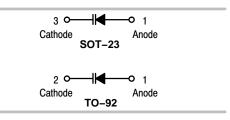
Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I <sub>R</sub> = 10 μAdc)	$V_{(BR)R}$	30	ı	1	Vdc
Reverse Voltage Leakage Current (V <sub>R</sub> = 25 Vdc)	I <sub>R</sub>	-	-	0.1	μAdc
Diode Capacitance Temperature Coefficient (V <sub>R</sub> = 3.0 Vdc, f = 1.0 MHz)	TC <sub>C</sub>	-	300	-	ppm/°C



#### ON Semiconductor®

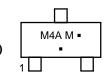
http://onsemi.com

# 26-32 pF VOLTAGE VARIABLE CAPACITANCE DIODES



#### MARKING DIAGRAMS

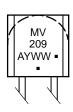




M4A = Device Code

(Note: Microdot may be in either location)\*Date Code orientation and/or overbar may vary depending upon manufacturing location.





MV209 = Device Code A = Assembly Location

Y = Year
WW = Work Week
Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

			$C_t$ , Diode Capacitance $V_R = 3.0 \text{ Vdc}$ , $f = 1.0 \text{ MHz}$ pF		$V_R = 3.0 \text{ Vdc}, f = 1.0 \text{ MHz}$ $V_R = 3.0 \text{ Vdc}$		C <sub>R</sub> , Capacitance Ratio C <sub>3</sub> /C <sub>25</sub> f = 1.0 MHz (Note 1)	
Device	Package	Shipping <sup>†</sup>	Min	Nom	Max	Min	Min	Max
MMBV109LT1	SOT-23	3,000 / Tape & Reel						
MMBV109LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel				32 200	5.0	6.5
MMBV109LT3	SOT-23	10,000 / Tape & Reel		26 29	29 32			
MMBV109LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel	26					
MV209	TO-92	1,000 Units / Bag						
MV209G	TO-92 (Pb-Free)	1,000 Units / Bag						

<sup>1.</sup>  $C_R$  is the ratio of  $C_t$  measured at 3 Vdc divided by  $C_t$  measured at 25 Vdc.

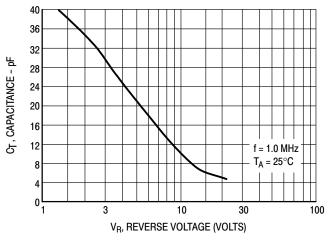


Figure 1. DIODE CAPACITANCE

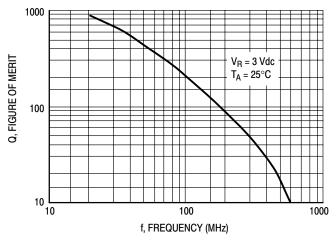


Figure 2. FIGURE OF MERIT

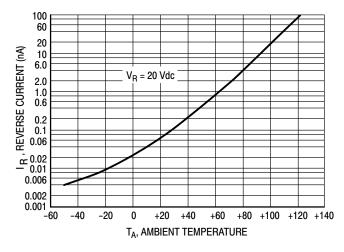


Figure 3. LEAKAGE CURRENT

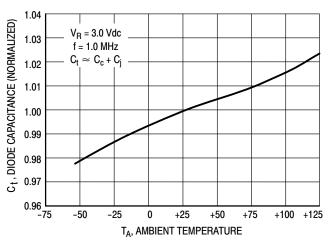
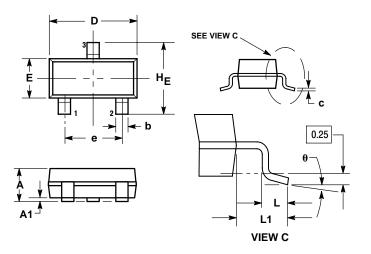


Figure 4. DIODE CAPACITANCE

#### NOTES ON TESTING AND SPECIFICATIONS

### **PACKAGE DIMENSIONS**

SOT-23 (TO-236) CASE 318-08 **ISSUE AN** 



#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

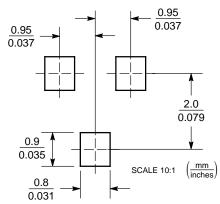
  4. 318–01 THRU –07 AND –09 OBSOLETE, NEW STANDARD 318–08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

#### STYLE 8:

- ANODE NO CONNECTION CATHODE

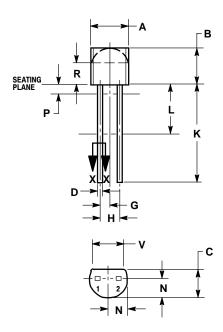
#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

**TO-92 (TO-226AC)** CASE 182-06 ISSUE L





**SECTION X-X** 

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
   V14 FM 1092
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- 3. CONTOUR OF PACKAGE BEYOND ZONE R IS UNCONTROLLED.
- 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.21	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.050	BSC	1.27 BSC		
Н	0.100 BSC		2.54	BSC	
J	0.014	0.016	0.36	0.41	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.03	2.66	
Р		0.050		1.27	
R	0.115		2.93		
V	0.135		3.43		

STYLE 1: PIN 1. ANODE

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